

Classical and *ab initio* molecular dynamic simulation of an amorphous silica surface

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Abstract

We present the results of a classical molecular dynamic simulation as well as of an *ab initio* molecular dynamic simulation of an amorphous silica surface. In the case of the classical simulation we use the potential proposed by van Beest *et al.* (BKS) whereas the *ab initio* simulation is done with a Car-Parrinello method (CPMD). We find that the surfaces generated by BKS have a higher concentration of defects (e.g. concentration of two-membered rings) than those generated with CPMD. In addition also the distribution functions of the angles and of the distances are different for the short rings. Hence we conclude that whereas the BKS potential is able to reproduce correctly the surface on the length scale beyond ≈ 5 Å, it is necessary to use an *ab initio* method to predict reliably the structure at small scales.

Key words: glass surface; silica; molecular dynamics simulations; *ab initio* simulations

1. Introduction

Obtaining a good understanding of the structural and dynamical properties of the surface of amorphous silica is very important for the manufacture of glass as well as the construction of electronic devices [1]. This is the reason why in the past a large number of experiments have been done to investigate this type of surface. Since in real experiments it is rather difficult to obtain reliably details on the structure also quite a few computer simulations have been done in order to study this system (see [2] and references therein). Most of these studies have, however, been done by using effective classical potentials, such as, e.g., the one pro-

posed some years ago by van Beest, Kramer, and van Santen (BKS) [3]. Although it has been shown that these type of potentials can reproduce quite reliably the structure and dynamics of silica in the *bulk* (see, e.g., [4] and references therein), it is much less obvious to what extent they are also able to give a correct description of the properties of silica close to a surface, since the parameters for these potentials, effective charges, etc., have often been optimized to reproduce only experimental data for the bulk. One possibility to avoid this problem with the classical effective potential is to use *ab initio* simulations such as the scheme proposed by Car and Parrinello [5] since in this type of approach an effective potential between the ions is calculated

self consistently on the fly, i.e. the instantaneous geometry of the ions is always taken into account. The drawback of this approach is that due to the huge computational burden only relatively short time scales, a few ps, as well as small systems, a few hundred particles, can be simulated, whereas classical simulations allow to simulate thousands of particles over several ns.

In the present work we compare the results of a classical simulation of an amorphous silica surface with the BKS potential with the results obtained by the Car-Parrinello Molecular Dynamics method (CPMD). The goal is to check which quantities are reproduced correctly by the BKS potential, using the results of the CPMD simulation as the reference system.

2. The BKS potential and the setup of the geometry

We have first prepared the system using the BKS potential. In this two-body potential the atoms interact also by means of a Coulomb potential where the effective charges of a silicon and oxygen atom is 2.4 and -1.2 , respectively. More details on this potential can be found in Ref. [3].

In order to minimize finite size effects as well as surface effects it is customary to use periodic boundary conditions (PBC) in all three directions. If one wants to investigate a free surface, the most straightforward idea is to use a film geometry, i.e. to have PBC in two directions and to have an infinite free space above and below the system. Unfortunately it turns out, however, that from a computational point of view this setup is not very good for systems with Coulombic interactions (i.e. such as the one studied here), since it prevents to make an *efficient* use of the Ewald summation method. Therefore we have adopted the following strategy which is explained also in Fig. 1 (see also [6,7]): i) We start with a relatively large (bulk) silica system at $T = 3400$ K with PBC in three dimension (with box size $L_x = L_y = 11.51\text{\AA}$ and $L'_z = 23\text{\AA}$). ii) We cut the system perpendicular to the z -direction into two pieces. Without loss of generality we can assume that the mean position of this cut is at

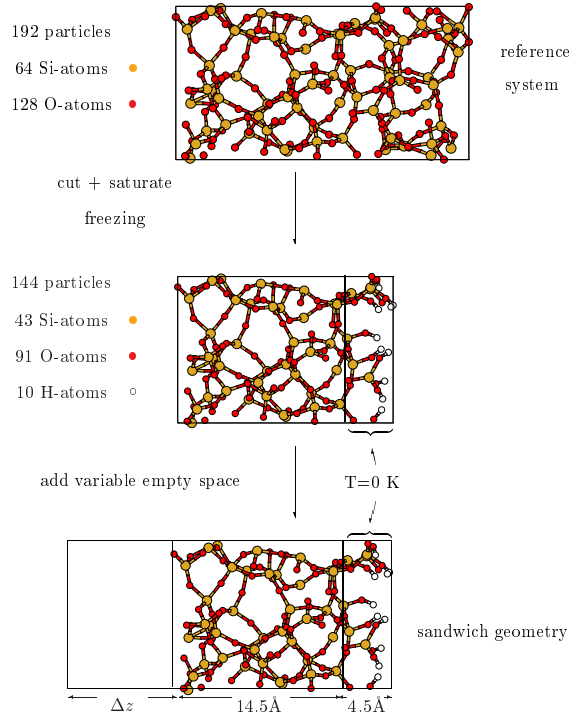


Fig. 1. Procedure to create the used sandwich geometry

$z = L'_z$. At this point it is very important, that we cut only oxygen-silicon-bonds, such that we get only free oxygen atoms at this interface (thus the interface will have a bit of roughness). iii) These free oxygen atoms are now saturated by hydrogen atoms. The place of these hydrogen atoms are chosen such that each of the new oxygen-hydrogen bonds is in the same direction as the oxygen-silicon bond which was cut and has a length of approximately $1\text{\AA}$. The interaction between the hydrogen atoms and the oxygen atoms as well as the silicon atoms are described only by a Coloumbic term. The value of the effective charge of the hydrogen atoms is set to 0.6, which ensures that the system is still (charge) neutral. iv) We make atoms which have a distance from this interface that is less than $4.5\text{\AA}$ completely immobile, whereas the atoms that have a larger distance can propagate subject to the force field. v) We add in z -direction an empty space of $\Delta z = 6.0\text{\AA}$ and thus generate a free surface at around $14.5\text{\AA}$. With this sandwich

geometry we now can use periodic boundary conditions in all three directions. We have made sure that the value of Δz is sufficiently large that the results do not depend on it anymore [8]. Note that it is not advisable to choose Δz too large, since this would increase the cost of the CPMD simulation. At the end of this procedure we have a system of 91 oxygen, 43 silicon and 10 hydrogen atoms in a simulation box with $L_x=L_y=11.51$ Å and $L_z \approx 25$ Å.

3. CPMD-Simulation

Since the time scale which is accessible to the CPMD-method is very restricted, we have to combine the *ab initio* with classical calculations. For this we first prepared a classical system as described in the previous section, equilibrated it for about 1 ns which is sufficient to equilibrate it completely [4]. From a subsequent production run with the same duration we picked 100 statistical independent configurations and used them to characterize the static properties of the system with a high accuracy. Using a subset of these configurations as starting points, we subsequently started CPMD-simulation using the CPMD code developed in Stuttgart [9]. For the CPMD we used conventional pseudopotentials for silicon and oxygen and the BLYP exchange-functions [10,11]. The electronic wave-functions were expanded in a plane wave basis set with an energy cutoff of 60 Ry and the equations of motion were integrated with a time step of 0.085 fs for 0.2 ps. In the analysis of the CMPD data only those configurations were taken into account that were produced later than 5 fs after the start of the CPMD run in order to allow the system to equilibrate at least locally [12].

In the analysis of the classical configurations we noted that typically one of the three following situations is present on the surface:

- systems with no defects (i.e. all Si and O atoms are four and two-fold coordinated, respectively)
- systems with an undercoordinated oxygen atom and an undercoordinated silicon atom
- systems with an overcoordinated oxygen atom and an undercoordinated oxygen atom

Therefore we picked for each case two BKS con-

figurations and started the CPMD runs.

The largest differences between the results of the classical and of the CPMD simulation are found for the short rings ($n < 5$). (A ring is a closed loop of n consecutive Si-O segments [13].) Figure 2 shows the probability to find a ring of size n for the case of BKS and CPMD. We see that the BKS potential overestimates the frequency with which a ring of size two occurs by about a factor of two. Related to this is the observation that the overshoot that is observed in the z -dependent mass density profile is less pronounced in the case of the CPMD than the one for the BKS (inset of Fig. 2), since two-membered rings are relatively dense.

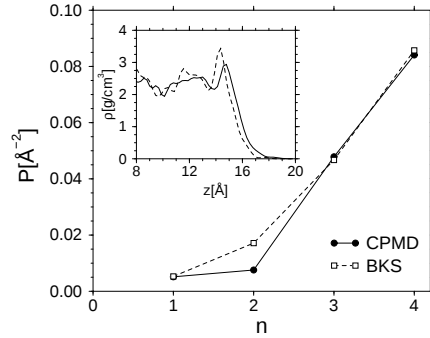


Fig. 2. Probability to find a ring of size n . Inset: z -dependence of the mass density.

From this inset we also see that the density profile for the CPMD extends to larger z values than the one for the BKS (by about 0.4 Å). This is because the BKS potential is not able to reproduce correctly the density of silica at zero pressure.

Another interesting result is the dependence of the distribution of angles O-Si-O on the ring size (Fig. 3). For large n , $n > 4$, i.e. the sizes which are normally found in the bulk [14], the results of the two different methods are in good agreement [12]. For smaller n , however, the mean O-Si-O-angle from CPMD is shifted to larger values in comparison to the classical one. This shift becomes more pronounced with decreasing n . Furthermore also the shape of the distributions starts to become different if n is small.

This effect can be understood better by analyzing the partial radial distribution functions $g(r)$ which are shown in Fig.4. We see that for the Si-O

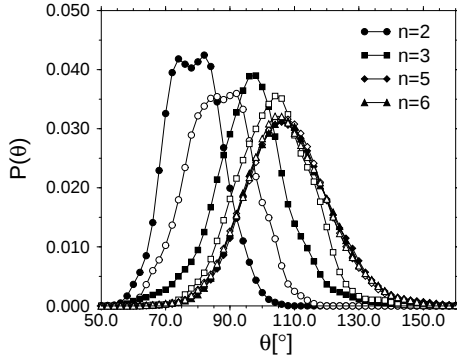


Fig. 3. Distribution of O-Si-O-angles for different ring sizes. BKS=filled symbols; CPMD=open symbols.

pair the curves from CPMD are shifted to larger distances by about $0.04 \text{ \AA}$ and that this shift is independent of n . Also the $g(r)$ for the O-O pairs are shifted to larger r , but this time the amount does depend on n . In particular we note that the O-O distance is nearly independent of n for the case of CPMD, whereas it increases with n for the case of BKS. These effects results in the difference in the distribution of the O-Si-O angles if n is small.

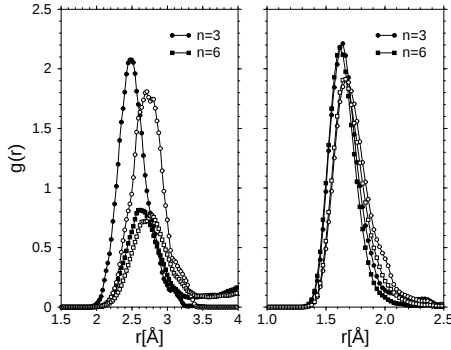


Fig. 4. Radial distribution function for different ring sizes. Left: O-O. Right Si-O. BKS=filled symbols; CPMD=open symbols.

4. Conclusion

In this work we have investigated some structural properties of an amorphous silica surface. In particular we have studied how these properties depend on the simulation method: A classical simula-

tion with the potential proposed by van Beest *et al.* (BKS) and a Car-Parrinello simulation (CPMD). We find that the structure on larger length scales are independent of the method used, whereas the details of structural elements on short scales (short rings, distribution function for angles, etc.) differ. Thus this shows that it is probably necessary to use *ab initio* methods if one wants to understand these systems at short length scales in a quantitative way.

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